

ISC Silicon NPN Power Transistor

2SC5855

DESCRIPTION

- · High speed switching
- · High voltage
- · Low saturation voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

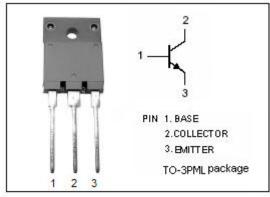


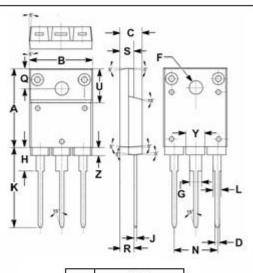
APPLICATIONS

- · Horizontal deflection output for super high resolution
- Display color TV digital TV



| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|---------|--------------|--|
| V _{CBO} | Collector-Base Voltage | 1500 | V | |
| V _{CEO} | Collector-Emitter Voltage | 700 | V | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | |
| Ic | Collector Current-Continuous | 10 | Α | |
| I _B | Base Current-Continuous | 5 | А | |
| Pc | Collector Power Dissipation @ T _C =25℃ 50 | | W | |
| TJ | Junction Temperature | 150 | $^{\circ}$ C | |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ C | |





| | mm | | | |
|-----|-------|-------|--|--|
| DIM | MIN | MAX | | |
| Α | 19.90 | 20.10 | | |
| В | 15.90 | 16.10 | | |
| C | 5.50 | 5.70 | | |
| D | 0.90 | 1.10 | | |
| F | 3.30 | 3.50 | | |
| G | 2.90 | 3.10 | | |
| Н | 5.90 | 6.10 | | |
| J | 0.595 | 0.605 | | |
| K | 22.30 | 22.50 | | |
| L | 1.90 | 2.10 | | |
| N | 10.80 | 11.00 | | |
| 0 | 4.90 | 5.10 | | |
| R | 3.75 | 3.95 | | |
| S | 3.20 | 3.40 | | |
| U | 9.90 | 10.10 | | |
| Y | 4.70 | 4.90 | | |
| Z | 1.90 | 2.10 | | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V _(BR) CEO | Collector-Emitter Breakdown Voltage | I _C =10mA; I _B = 0 | 700 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E =1mA; I _C = 0 | 5 | | | V |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C =8A; I _B = 2A | | | 3 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C =8A; I _B = 2A | | | 1.4 | V |
| Ісво | Collector Cutoff Current | V _{CB} = 1500V; I _E = 0 | | | 100 | μА |
| h _{FE-1} | DC Current Gain | I _C = 1A; V _{CE} = 5V | 28 | | 60 | |
| h _{FE-2} | DC Current Gain | I _C =6A; V _{CE} = 5V | 6.2 | | 10 | |
| h _{FE-3} | DC Current Gain | Ic=8A; VcE= 5V | 4.3 | | 6.7 | |

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